

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2579

DESCRIPTION

- With TO-3PN package
- High power dissipation
- High current capability

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

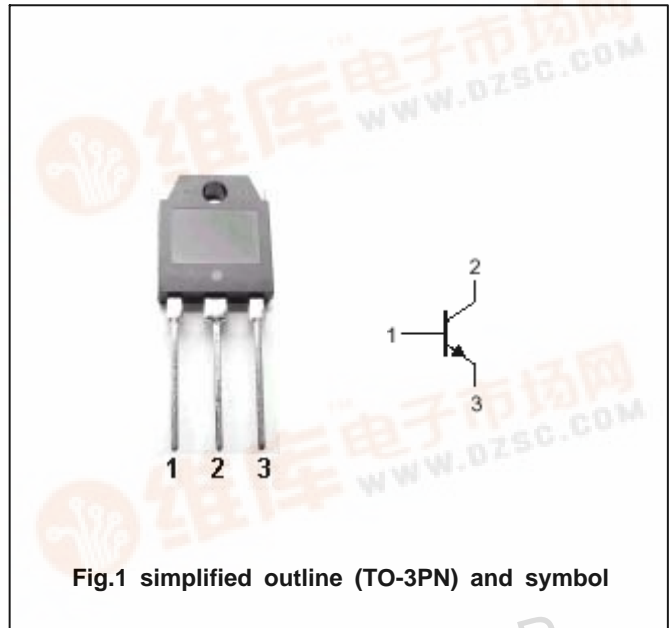


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	160	V
V _{CEO}	Collector-emitter voltage	Open base	160	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		8	A
P _C	Collector power dissipation	T _C =25	80	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =5mA; I _E =0	160			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; R _{BE} =	160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =5mA; I _C =0	6			V
I _{CBO}	Collector cut-off current	V _{CB} =160V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A; V _{CE} =4V	50			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.0	V
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V		20		MHz

